SiC JFET Division

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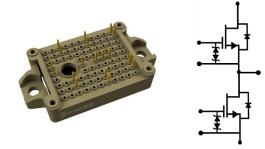
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Silicon Carbide (SiC) Cascode JFET Module - EliteSiC, Half-Bridge Module, 1200 V, 9.4 mohm

UHB100SC12E1BC3N

DATASHEET







Rev. D, January 2025

Description

This SiC FET device is based on a unique 'cascode' circuit configuration, in which a normally-on SiC JFET is co-packaged with a Si MOSFET to produce a normally-off SiC FET device. The device's silicon-like gate-drive characteristics allows the use of unipolar gate drives, compatible with Si IGBTs, Si FETs, SiC MOSFETs or Si superjunction devices. Available in the E1B module package, this device exhibits ultra-low gate charge and exceptional reverse recovery characteristics, making it ideal for switching inductive loads, and any application requiring standard gate drive. Advanced Ag sintering die attach technology gives the module superior thermal performance.

Features

- On-resistance: R_{DS(on)} = 9.4mΩ (typ)
- Operating temperature: 150°C (max)
- Excellent reverse recovery: Q_{rr} = 1000nC
- Low body diode voltage: V_{FSD} = 1.4V
- Low gate charge: Q_G = 170nC
- Threshold voltage V_{G(th)}: 5V (typ) allowing 0 to 15V drive
- Low intrinsic capacitance
- ESD protected: HBM class 2 and CDM class C3

Typical applications

- EV charging
- PV inverters
- Switch mode power supplies
- Power factor correction modules
- Motor drives
- Induction heating





Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-source voltage	V _{DS}		1200	V
Gate-source voltage		DC	-20 to +20	V
	V _{GS}	AC (f > 1Hz)	-25 to +25	V
Continuous drain current ¹	I _D	T _C < 85°C	100	Α
Pulsed drain current ²	I _{DM}	T _C = 25°C	700	Α
Power dissipation per switch	P _{tot}	T _C = 25°C	417	W
Maximum junction temperature	T _{J,max}		150	°C
Operating and storage temperature	T _J , T _{STG}		-55 to 150	°C

1. Limited by package lead count

2. Pulse width t_p limited by $T_{J,max}$

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			Units	
			Min	Тур	Max	Onits	
Thermal resistance, junction-to-case	D			0.23	0.3	°C/W	
per switch	$R_{ ext{ hetaJC}}$			0.25	0.5	C/ VV	

NTC Thermistor Characteristics

Parameter	Symphol	Test Conditions		Units		
	Symbol	Test Conditions	Min	Тур	Max	Units
Rated resistance	R ₂₅	T _{NTC} = 25°C		5		kΩ
Resistance value tolerance	$\Delta R/R$	T _{NTC} = 25°C	-5		5	%
Power dissipation	P ₂₅	T _{NTC} = 25°C			20	mW
B constant	B _{25/50}	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$		3375		к

Module

Parameter	Symbol	Test Conditions	Value	Units
Isolation voltage	V _{ISOL}	RMS, f = 50 Hz, t = 1 min	3	kV
Internal isolation			Al ₂ O ₃	
Creanage distance		Terminal to heatsink	12.7	mm
Creepage distance		Terminal to terminal	6.3	mm
Clearance distance		Terminal to heatsink	10	mm
		Terminal to terminal	5	mm
Stray inductance module	L _{sCE}		11	nH

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SiC FET Electrical Characteristics (T_J = +25°C unless otherwise specified)

Typical Performance - Static

Parameter	Symbol	Test Conditions		Value		– Units	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units	
Drain-source breakdown voltage	BV _{DS}	V _{GS} =0V, I _D =8mA	1200			V	
Total drain leakage current		V _{DS} =1200V,		32	600		
		V _{GS} =0V, T _J =25°C		32	800		
	DSS	V _{DS} =1200V,		100		μΑ	
		V _{GS} =0V, T _J =150°C					
Total gate leakage current	1	V _{DS} =0V, T _J =25°C,		24	80	μΑ	
	I _{GSS}	V _{GS} =-20V / +20V					
		V _{GS} =12V, I _D =70A,		9.4	12		
		TJ=25°C					
Drain-source on-resistance	R _{DS(on)}	V _{GS} =12V, I _D =70A,		4.5		mΩ	
Drain source on resistance	US(on)	T _J =125°C		15		11152	
		V _{GS} =12V, I _D =70A,		17.5			
		T_=150°C		17.5			
Gate threshold voltage	V _{G(th)}	V_{DS} =5V, I_{D} =40mA	4	5	6	V	
Gate resistance	R _G	f=1MHz, open drain		1.1		Ω	

Typical Performance - Reverse Diode

Deveryeter	Symbol	Test Conditions	Value			– Units	
Parameter			Min	Тур	Max	Units	
Diode continuous forward current ¹	I _S	T _C < 85 °C			100	A	
Diode pulse current ²	I _{S,pulse}	T _C =25°C			700	А	
Forward voltage	V _{FSD}	V _{GS} =0V, I _S =70A, T _J =25°C		1.4	2	V	
	♥ FSD	V _{GS} =0V, I _S =70A, T _J =150°C		1.63			
Reverse recovery charge	Q _{rr}	V_{DS} =800V, I _S =100A, V_{GS} =-5V, R _G =5 Ω		1000		nC	
Reverse recovery time	t _{rr}	di/dt=4100A/µs, T_=25°C		41		ns	
Reverse recovery charge	Q _{rr}	V_{DS} =800V, I _S =100A, V_{GS} =-5V, R _G =5Ω		920		nC	
Reverse recovery time	t _{rr}	di/dt=4100A/μs, Τ _J =150°C		40		ns	





Typical Performance - Dynamic

Darameter	Parameter Symbol Test Co				L Institus	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Input capacitance	C _{iss}	V _{DS} =800V, V _{GS} =0V		5859		
Output capacitance	C _{oss}			372		pF
Reverse transfer capacitance	C _{rss}	- f=100kHz		6.7		
Effective output capacitance, energy	6	V _{DS} =0V to 800V,		400		
related	C _{oss(er)}	V _{GS} =0V		480		pF
Effective output capacitance, time	6	V _{DS} =0V to 800V,		10/5		
related	C _{oss(tr)}	V _{GS} =0V		1065		pF
C _{OSS} stored energy	E _{oss}	V _{DS} =800V, V _{GS} =0V		154		μJ
Total gate charge	Q _G	- V _{DS} =800V, I _D =100A, - V _{GS} = -5V to 15V -		170		
Gate-drain charge	Q_{GD}			38		nC
Gate-source charge	Q _{GS}			62]
Turn-on delay time	t _{d(on)}	- Notes 3 and 4 - V _{DS} =800V, I _D =100A, Gate -		50		
Rise time	t _r			33]
Turn-off delay time	t _{d(off)}			65		ns
Fall time	t _f	– Driver =-5V to +15V, – R _{G EXT} =5Ω, Inductive Load, –		12		
Turn-on energy	E _{ON}	$- FWD: V_{GS} = -5V,$		1442		
Turn-off energy	E _{OFF}	$R_{G EXT} = 5\Omega, T_J = 25^{\circ}C$		308		μ]
Total switching energy	E _{TOTAL}	$-10^{-10} \text{G}_{\text{EXT}} - 522, 15^{-2} \text{C}$		1750		
Turn-on delay time	t _{d(on)}	Notes 3 and 4		45		
Rise time	t _r			31		
Turn-off delay time	t _{d(off)}	 V_{DS}=800V, I_D=100A, Gate Driver =-5V to +15V, 		70		ns
Fall time	t _f			11		
Turn-on energy	E _{ON}	$-R_{G_{EXT}}=5\Omega$, Inductive Load, $-$ FWD: V _{GS} = -5V, -		1280		
Turn-off energy	E _{OFF}			266		μ]
Total switching energy	E _{TOTAL}	R _{G_EXT} = 5Ω, T _J =150°C		1546		

3. Measured with the half-bridge mode switching test circuit in Figure 23.

4. A bus RC snubber (R_{BS} = 2.5 Ω , C_{BS} =200nF) must be applied to reduce the power loop high frequency oscillations.





Typical Performance - Dynamic (continued)

		T I C IVI	Value			
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Turn-on delay time	t _{d(on)}			27.2		
Rise time	t _r	Notes 5 and 6, V_{DS} =800V, I_D =100A, Gate Driver =-5V to +15V, $R_{G,EXT} = 1\Omega$, inductive Load, FWD: same device with V_{GS} = -5V and R_G = 1 Ω , RC snubber: R_S =5 Ω and C_S =440pF, T_J =25°C		18.4		ns
Turn-off delay time	t _{d(off)}			57.6		
Fall time	t _f			16		-
Turn-on energy including R _s energy	E _{ON}			510		
Turn-off energy including R _s energy	E _{OFF}			518		μ μ
Total switching energy	E _{TOTAL}			1028		
Snubber R _s energy during turn-on	E _{RS_ON}			30		
Snubber R _s energy during turn-off	E _{RS_OFF}			28		
Turn-on delay time	t _{d(on)}			28		
Rise time	t _r	Notes 5 and 6,		13.6		
Turn-off delay time	t _{d(off)}	V _{DS} =800V, I _D =100A, Gate Driver =-5V to +15V,		61.6		ns
Fall time	t _f	$R_{G,EXT} = 1\Omega,$		18.4		
Turn-on energy including R _s energy	E _{ON}	inductive Load,		382		
Turn-off energy including R _s energy	E _{OFF}	FWD: same device with - V _{GS} = -5V and R _G = 1Ω, RC - snubber: R _S =5Ω and		521		
Total switching energy	E _{TOTAL}			903		μ
Snubber R _s energy during turn-on	E _{RS_ON}	С _s =440pF, T _j =150°С		30		
Snubber R _s energy during turn-off	E _{RS_OFF}			25		1

5. Measured with the switching test circuit in Figure 24.

6. In this table, the switching energies (turn-on energy, turn-off energy and total energy) presented include the device RC snubber energy losses.

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SiC FET Typical Performance Diagrams

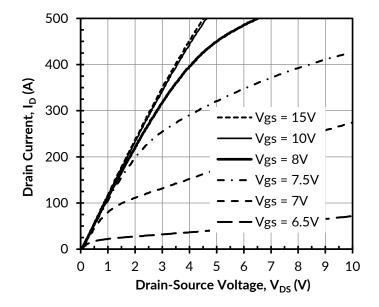
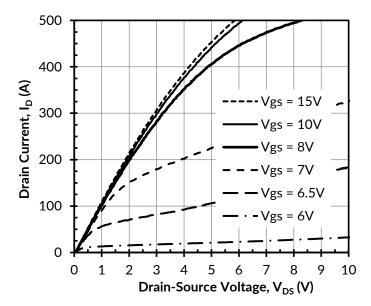


Figure 1. Typical output characteristics at $T_J = -55^{\circ}C$, tp < 250 μ s



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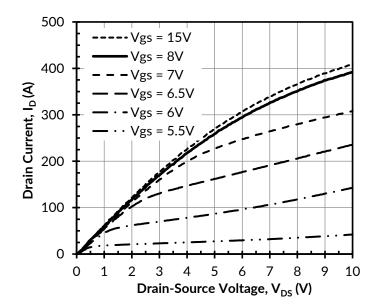
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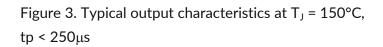
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Figure 2. Typical output characteristics at $T_{\rm J}$ = 25°C, tp < 250 μs





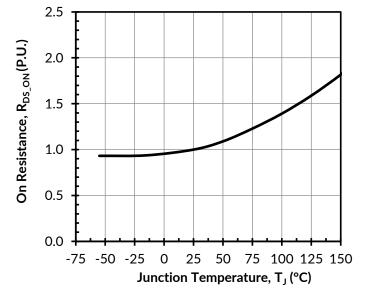


Figure 4. Normalized on-resistance vs. temperature at V_{GS} = 12V and I_D = 70A

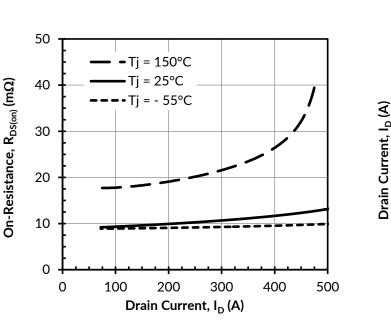


Figure 5. Typical drain-source on-resistances at V_{GS} = 12V

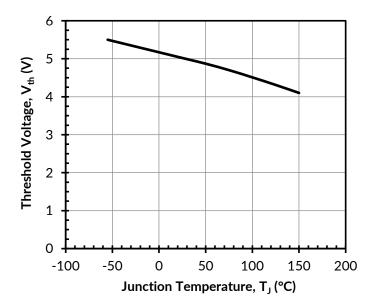
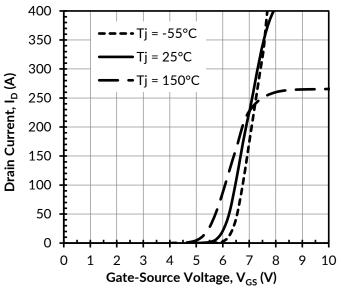


Figure 7. Threshold voltage vs. junction temperature at V_{DS} = 5V and I_D = 40mA



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Figure 6. Typical transfer characteristics at V_{DS} = 5V

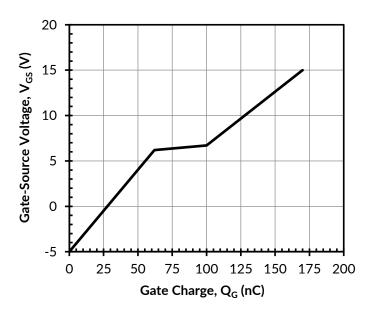
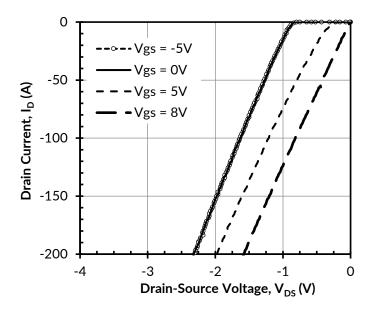


Figure 8. Typical gate charge at V_{DS} = 800V and I_{D} = 100A

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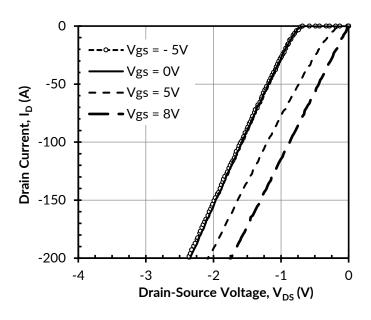


Figure 9. 3rd quadrant characteristics at $T_{J} = -55^{\circ}C$

Figure 10. 3rd quadrant characteristics at T_J = 25°C

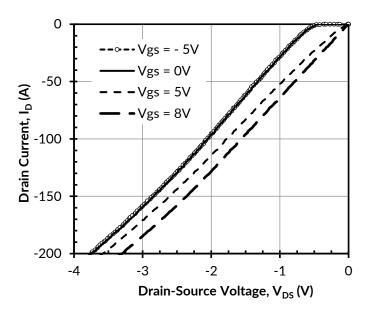


Figure 11. 3rd quadrant characteristics at $T_J = 150^{\circ}C$

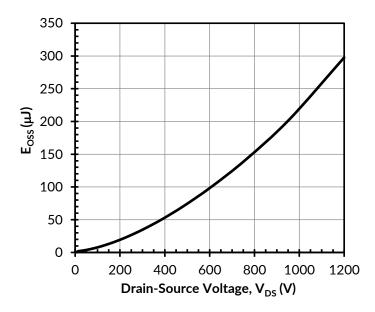


Figure 12. Typical stored energy in C_{OSS} at V_{GS} = 0V

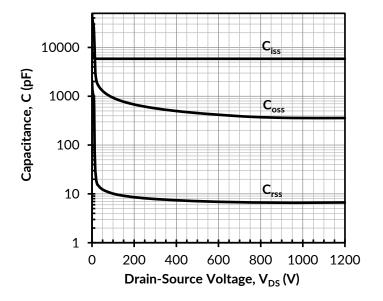
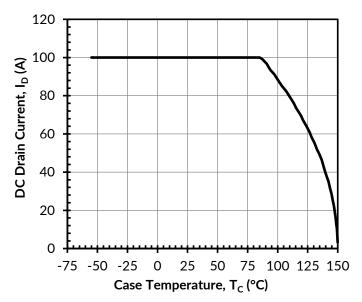


Figure 13. Typical capacitances at f = 100kHz and V_{GS} = 0V



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Figure 14. DC drain current derating

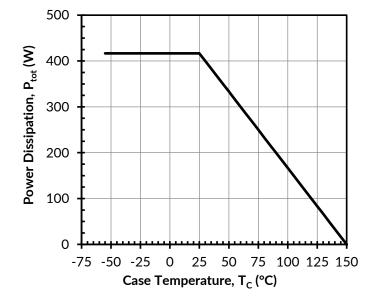


Figure 15. Total power dissipation

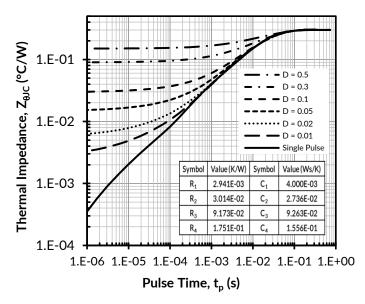


Figure 16. Maximum transient thermal impedance and parameters for thermal equivalent circuit (Foster) model



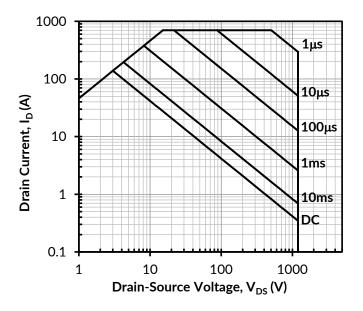


Figure 17. Safe operation area at T_C = 25°C, D = 0, Parameter t_p

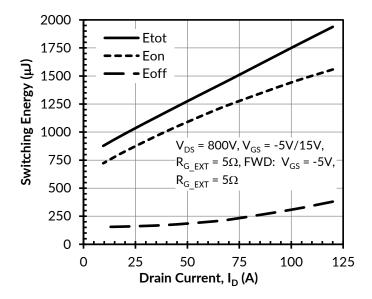


Figure 18. Clamped inductive switching energy vs. drain current at $T_J = 25^{\circ}C$

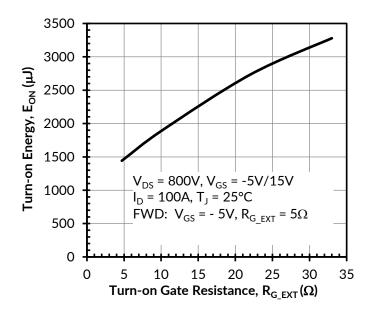


Figure 19. Clamped inductive switching turn-on energy vs. turn-on gate resistance R_G

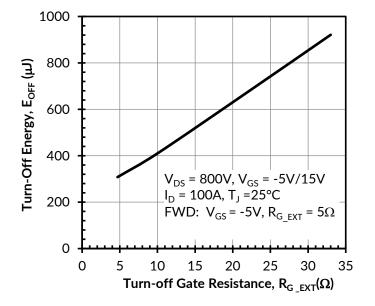


Figure 20. Clamped inductive switching turn-off energy vs. turn-off gate resitiance R_G



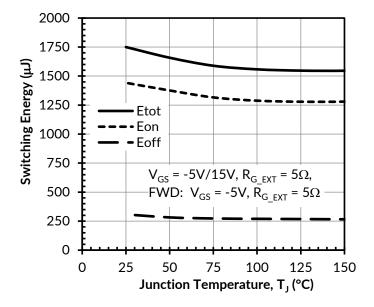


Figure 21. Clamped inductive switching energy vs. junction temperature at V_{DS} = 800V and I_D = 100A

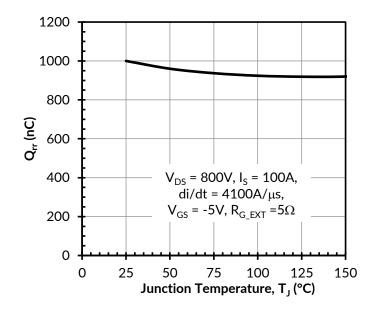


Figure 22. Reverse recovery charge Q_{rr} vs. junction temperature

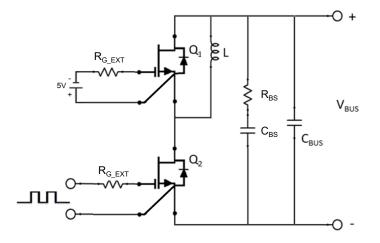


Figure 23. Schematic of the half-bridge mode switching test circuit. Note, a bus RC snubber (R_{BS} = 2.5 Ω , C_{BS} =200nF) must be applied to reduce the power loop high frequency oscillations.

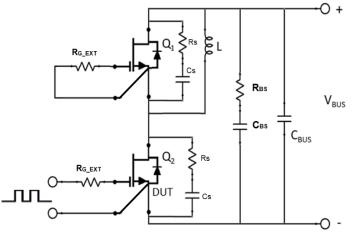
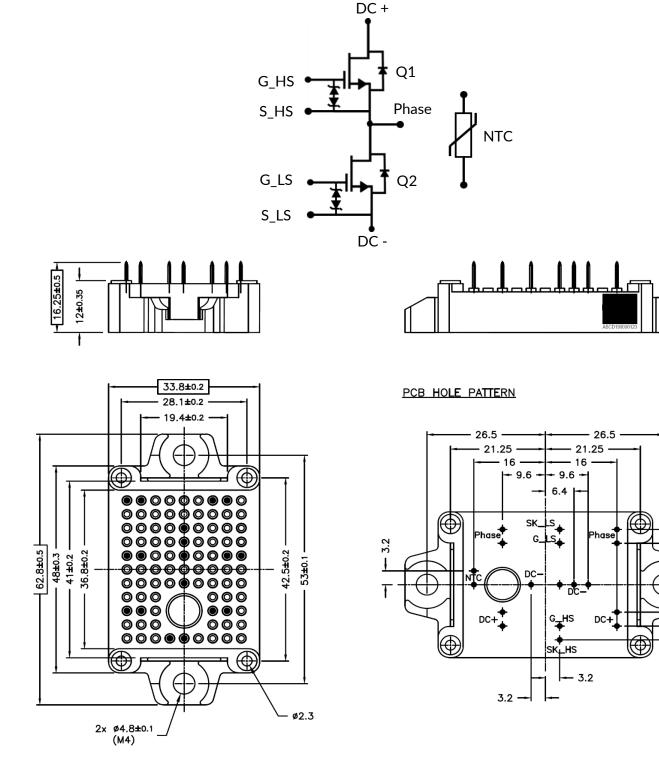


Figure 24. Schematic of the half-bridge mode switching test circuit with device RC snubbers (R_s =5 Ω , C_s = 440pF) and a bus RC snubber (R_{BS} = 2.5 Ω , C_{BS} =200nF).





Circuit Diagram and Pin Definitions



NOTES:

- 1.
- All dimensions in millimeters (mm) General tolerance: ± 0.1mm, unless otherwise 2. specified

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Important Mounting Information

This product is recommended for use with solder pin attach and phase change thermal interface materials, and not recommended for implementations using press fit and application of thermal grease. Please refer to mounting guidelines and user guide documents associated with this product for detailed information.

Applications Information

SiC FETs are enhancement-mode power switches formed by a high-voltage SiC depletion-mode JFET and a low-voltage silicon MOSFET connected in series. The silicon MOSFET serves as the control unit while the SiC JFET provides high voltage blocking in the off state. This combination of devices in a single package provides compatibility with standard gate drivers and offers superior performance in terms of low on-resistance ($R_{DS(on)}$), output capacitance (C_{oss}), gate charge (Q_G), and reverse recovery charge (Qrr) leading to low conduction and switching losses. The SiC FETs also provide excellent reverse conduction capability eliminating the need for an external anti-parallel diode.

Like other high performance power switches, proper PCB layout design to minimize circuit parasitics is strongly recommended due to the high dv/dt and di/dt rates. An external gate resistor is recommended when the FET is working in the diode mode in order to achieve the optimum reverse recovery performance. For more information on SiC FET operation, see https://www.qorvo.com/innovation/power-solutions/sic-power/sic-fet-design-tips.

A snubber circuit with a small $R_{(G)}$, or gate resistor, provides better EMI suppression with higher efficiency compared to using a high $R_{(G)}$ value. There is no extra gate delay time when using the snubber circuitry, and a small $R_{(G)}$ will better control both the turn-off $V_{(DS)}$ peak spike and ringing duration, while a high $R_{(G)}$ will damp the peak spike but result in a longer delay time. In addition, the total switching loss when using a snubber circuit is less than using high $R_{(G)}$, while greatly reducing $E_{(OFF)}$ from mid-to-full load range with only a small increase in $E_{(ON)}$. Efficiency will therefore improve with higher load current. For more information on how a snubber circuit will improve overall system performance, visit the Qorvo website at https://www.qorvo.com/innovation/power-solutions/sic-power/sic-fet-design-tips.

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E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

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MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Introduction

This Manufacturing Note is intended for manufacturing engineers who are currently using the module for prototype or production manufacturing. The information provided in this document is meant to assist customers with the set-up and characterization of their products.

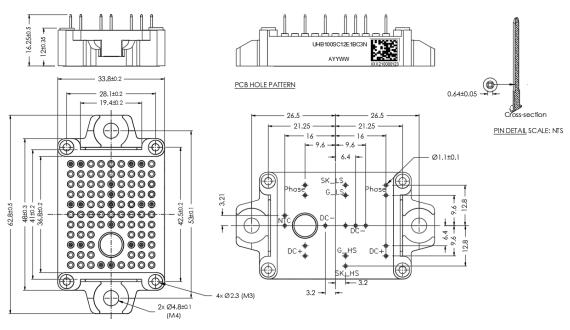
Module Package Description

This module is a SiC FET device based on a unique cascode circuit configuration, in which a normally-on SiC JFET is co-packaged with a Si MOSFET to produce a normally-off SiC FET device. The device's silicon-like gate-drive characteristics allows the use of unipolar gate drives, compatible with Si IGBTs, Si FETs, SiC MOSFETs or Si superjunction devices. Available in the E1B module package, this device exhibits ultra-low gate charge and exceptional reverse recovery characteristics, making it ideal for switching inductive loads, and any application requiring standard gate drive Package Outline Drawing.

Package Outline Drawing

This product is recommended for use with solder pin attach and phase change thermal interface materials, and not recommended for implementations using press fit and application of thermal grease. Please refer to mounting guidelines and user guide documents associated with this product for detailed information.

Package outline for Half Bridge modules: UHB100SC12E1BC3N & UHB50SC12E1BC3N

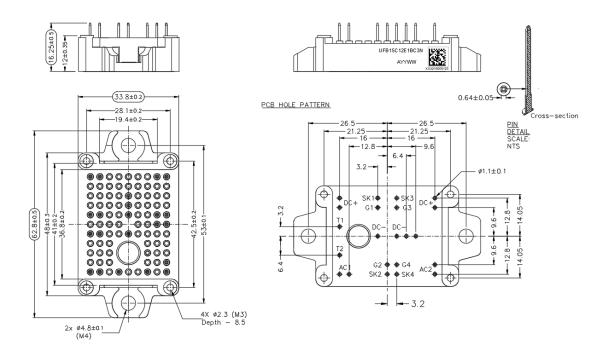


NOTES:

- 1. All dimensions in millimeters (mm)
- 2. General tolerance: \pm 0.1mm, unless otherwise specified

MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Package outline for Full Bridge modules: UFB15C12E1BC3N & UFB25SC12E1BC3N



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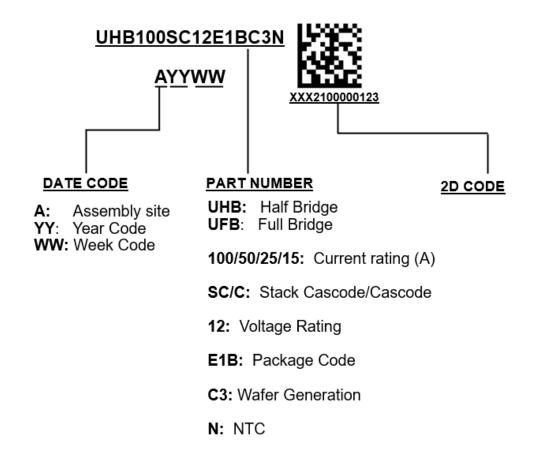
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2. General tolerance: ± 0.1mm, unless otherwise specified



MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Branding Diagram (Marking)



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MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Carriers

Tray and Shipping Instructions

The module is placed in an ESD tray with a pocket carrier that holds the module in dead bug orientation. The pocket is designed to hold the module for shipping and for loading onto manufacturing equipment, while protecting the body and the solder pins from damaging stresses with a lid to seal the units firmly. Then trays are placed in a shipping box with desiccant, proper label, and protective packaging so secure the tray firmly prior packing with tape.

The individual tray pocket design and count can vary from vendor to vendor.

Tray

1. Tray size and specification for large quantity

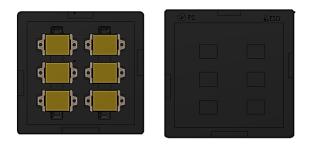
Tray size: 356x276x30 mm Material: PS Unit Quantity per tray: 24 pcs



Figure 1

2. Tray size and specification for small quantity

Tray size: 199x192x31 mm Material: PS Unit Quantity per tray: 6 pcs







MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Storage and Handling

Storage and Handling Conditions

Excessive forces from shock or vibration as well as environmental factors must be avoided when transporting and handling the modules. Although it is not advised, it is feasible to store the modules at the temperature ranges listed in the datasheet. Furthermore, the modules can be subjected to environmental conditions, see reference below.

IEC 60721-3-1: Classification of environmental conditions.

IEC 60721- 3-2: Classification of groups of environmental parameters and their severities - Transportation and handling/

IEC 60721-3-3 Classification of groups of environmental parameters and their severities – Stationary use at weather protected locations.

ESD

Electrostatic discharge occurs naturally in the environment. With the increase in voltage potential, the outlets of neutralization or discharge will be sought. If the acquired discharge route is through a semiconductor device, destructive damage will result.

ESD countermeasure methods should be developed and used to Control potential ESD damage during handling in a factory environment at each manufacturing site.

This part is considered ESD sensitive and needs to be handled accordingly.

Qorvo recommends using standard ESD precautions (see Reference Documents) when handling these devices.

Reference Documents:

- 1. JEDEC Standard JESD625-A, "Requirements for Handling Electrostatic-Discharge-Sensitive (ESDS) Devices."
- 2. ANSI/ESD S20.20, "Protection of Electrical and Electronic Parts, Assemblies and Equipment (Excluding Electrically Initiated Explosive Devices)."

NOTE: The ESD level for this part is documented in the product qualification report that is available from Qorvo.

MANUFACTURING NOTE: E1B PACKAGE OUTLINE, PART MARKING and TRAY SPECIFICATION

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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Tel: +1 833-641-3811

Email: customer.support@gorvo.com

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